

Agenda - Si and SiGe Epitaxy Users Meeting

Tuesday 3.11.2026 - Afternoon Session

12:30 *Arrival*

Opening

13:00	Matthias Künle & Malte Czernohorsky	Bosch, Fraunhofer IPMS	Welcome and Introduction
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Batch Epitaxy Processing

13:20	Charlotte Weiss	Fraunhofer ISE	Si, SiGe and Ge Epitaxy at Fraunhofer ISE
13:40	Taku Kikuchi	Kokusai	Productivity and Quality Improvement in Batch Si/SiGe Epitaxy

Epitaxy Processes

14:00	Elias Haar	Bosch	A versatile deposition process for thick, highly in-situ-doped polycrystalline Silicon layers and their electrical and microstructural characterization
14:20	Yuji Yamamoto	IHP - Leibniz-Institut für innovative Mikroelektronik	Atomic-Layer Epitaxy Process for Advanced Group-IV Device Application
14:40	Annekathrin Zeun	Globalfoundries	EPI chamber particle performance - Preprocessing conditions

15:00 *Coffee break & networking*

Epitaxy Contamination & Defects

15:30	Terence Mittmann	Infineon	Unexpected Chamber Contamination: Restoring Lifetime with a New Clean
15:50	Stella Van Eek	Bosch	Slip Lines Mitigation Strategy for ATM Si EPI

Metrology & Simulation

16:10	Adrian Adrian	LayTec AG	In-situ epitaxy monitoring by pyrometry, reflectance and deflection analysis
16:30	Andrey Smirnov	STR	Modeling of thickness uniformity and interface sharpness in Si/SiGe epitaxy

17:30 *End of Day 1*

19:00 *Evening Event @ Watzke am Goldenen Reiter*

Wednesday 4.11.2026 - Morning session

08:45	Arrival		
	Welcome Day 2		
09:00	Marion Drießen & Olaf Fiedler	Fraunhofer ISE, Infineon	Wrap up day 1
	Epitaxy Processes		
09:10	Shohei Fukaya	IHP - Leibniz-Institut für innovative Mikroelektronik	Effect of HCl on Disilane-based Crystalline and Amorphous Si growth by Reduced-Pressure Chemical Vapor Deposition
09:30	Ivo Rahlff	Leibniz-Institut für Kristallzüchtung	Sub-nm Ge Concentration Oscillations in Si/SiGe: MBE Growth and Characterization
09:50	Kei Kiyose	IHP - Leibniz-Institut für innovative Mikroelektronik	Initial Surface Reaction of Ge on Si adsorbed Ge Surface Formed by Atomic Layer Epitaxy
	Metrology		
10:10	Andreas Nollau	Semilab Zrt.	Room Temperature Photoluminescence Detection of Defects on Si/SiGe Superlattice Samples
10:30	René Chemnitzer	CAMECA	Advancing Epitaxial Layer Characterization with Dynamic SIMS: New Opportunities for Sensitivity and Depth Resolution
10:50	Coffee break & networking		
	Epitaxy Hardware		
11:20	Dino Alagic	Schunk Xycarb Technology	Upgrading EPI Performance by Tuning Hardware Parts to Your Process Needs
11:40	Steve Burch	Helios Technical Services	Helios SiGe
	Epitaxy Facilities		
12:00	Matthias Künle	Bosch	Preventing exhaust line incidents in Si epitaxy: chemical analysis and safe handling of pyrophoric residues
	Closing of meeting		
12:20	All		Wrap up of Si and SiGe Epitaxy Users Meeting
13:00	End of Day 2		